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REGULAR PAPERS

Silicon and Column IV Semiconductors Devices

| | | |
|---|---|------|
| Small-Signal Capacitance and Current Parameter Modeling in Large-Scale High-Frequency Graphene Field-Effect Transistors | <i>G. I. Zebrev, A. A. Tselykovskiy, D. K. Batmanova, and E. V. Melnik</i> | 1799 |
| Device and Circuit Performance Estimation of Junctionless Bulk FinFETs | <i>M.-H. Han, C.-Y. Chang, H.-B. Chen, Y.-C. Cheng, and Y.-C. Wu</i> | 1807 |
| Comprehensive Analysis of Short-Channel Effects in Ultrathin SOI MOSFETs | <i>Q. Xie, C.-J. Lee, J. Xu, C. Wann, J. Y.-C. Sun, and Y. Taur</i> | 1814 |
| Gate All Around MOSFET With Vacuum Gate Dielectric for Improved Hot Carrier Reliability and RF Performance | <i>R. Gautam, M. Saxena, R. S. Gupta, and M. Gupta</i> | 1820 |
| Comparison of ZnO-Based JFET, MESFET, and MISFET | <i>F. J. Klüpfel, F.-L. Schein, M. Lorenz, H. Frenzel, H. von Wenckstern, and M. Grundmann</i> | 1828 |
| Compact Model for Carbon Nanotube Field-Effect Transistors Including Nonidealities and Calibrated With Experimental Data Down to 9-nm Gate Length | <i>J. Luo, L. Wei, C.-S. Lee, A. D. Franklin, X. Guan, E. Pop, D. A. Antoniadis, and H.-S. P. Wong</i> | 1834 |
| Time and Frequency Domain Characterization of Transistor Self-Heating | <i>S. Makovejev, S. H. Olsen, V. Kilchytska, and J.-P. Raskin</i> | 1844 |
| Germanium Multiple-Gate Field-Effect Transistors Formed on Germanium-on-Insulator Substrate | <i>B. Liu, X. Gong, C. Zhan, G. Han, H.-C. Chin, M.-L. Ling, J. Li, Y. Liu, J. Hu, N. Daval, C. Veytizou, D. Delprat, B.-Y. Nguyen, and Y.-C. Yeo</i> | 1852 |
| Surface-Roughness-Limited Mean Free Path in Silicon Nanowire Field Effect Transistors | <i>H.-E. Jung and M. Shin</i> | 1861 |
| An Effective Capacitance Model for 28-nm and Beyond Copper Interconnect | <i>Y. Xu, F. Bai, W. Liu, and C. Xie</i> | 1867 |

(Contents Continued on Page 1797)

| | | |
|---|--|------|
| Novel Vertical SOI-Based 1T-DRAM With Trench Body Structure | <i>J.-T. Lin, P.-H. Lin, Y.-C. Eng, and Y.-R. Chen</i> | 1872 |
| Epitaxial Germanium on SOI Substrate and Its Application of Fabricating High I_{ON}/I_{OFF} Ratio Ge FinFETs | <i>C.-T. Chung, C.-W. Chen, J.-C. Lin, C.-C. Wu, C.-H. Chien, G.-L. Luo, C.-C. Kei, and C.-N. Hsiao</i> | 1878 |
| Analysis of the Performance of n-Type FinFETs With Strained SiGe Channel | <i>D. Lizzit, P. Palestri, D. Esseni, A. Revelant, and L. Selmi</i> | 1884 |
| Half-MOS Single-Poly EEPROM Cell in Standard CMOS Process | <i>F. Torricelli, L. Milani, A. Richelli, L. Colalongo, M. Pasotti, and Z. M. Kovacs-Vajna</i> | 1892 |
| Compound Semiconductor Devices | | |
| Thermometry of AlGaIn/GaN HEMTs Using Multispectral Raman Features | <i>S. Choi, E. R. Heller, D. Dorsey, R. Vetury, and S. Graham</i> | 1898 |
| Field-Emission and Photoelectrical Characteristics of Ga-ZnO Nanorods Photodetector | <i>C.-H. Hsiao, C.-S. Huang, S.-J. Young, S.-J. Chang, J.-J. Guo, C.-W. Liu, and T.-Y. Yang</i> | 1905 |
| Influence of Dopants on the Thermal Conductance of GaN-Sapphire Interface | <i>H. Zheng and K. Jagannadham</i> | 1911 |
| Low-Interface-Trap-Density and High-Breakdown-Electric-Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition | <i>T. Watanabe, A. Teramoto, Y. Nakao, S. Sugawa, and T. Ohmi</i> | 1916 |
| Characterization and Modeling of 4H-SiC Lateral MOSFETs for Integrated Circuit Design | <i>M. Mudholkar and H. A. Mantooth</i> | 1923 |
| Thermal Parameter Extraction Method for Light-Emitting Diode (LED) Systems | <i>X. Tao and D. Zhang</i> | 1931 |
| Memory Devices and Technology | | |
| Thermal Modeling of Resistive Switching Devices | <i>A. T. Ramu and D. B. Strukov</i> | 1938 |
| Ferroelectric-Assisted Dual-Switching Speed DRAM-Flash Hybrid Memory | <i>S. R. Rajwade, T. A. Naoi, K. Auluck, K. Jayant, R. B. V. Dover, and E. C. Kan</i> | 1944 |
| Thin Film Transistors | | |
| Transparent Junctionless Electric-Double-Layer Transistors Gated by a Reinforced Chitosan-Based Biopolymer Electrolyte | <i>J. Jiang, Q. Wan, and Q. Zhang</i> | 1951 |
| Optoelectronics, Displays, and Imaging | | |
| Schottky Barrier Controlled Conduction in Poly-Si TFTs With Metal Source and Drain | <i>J. Chen, M. Wang, D. Zhang, P. Lv, and M. Wong</i> | 1958 |
| Bridged-Grain Polycrystalline Silicon Thin-Film Transistors | <i>S. Zhao, Z. Meng, W. Zhou, J. Ho, M. Wong, and H.-S. Kwok</i> | 1965 |
| Influence by Layer Structure on the Output EL of CMOS Compatible Silicon-Based Light Emitters | <i>A. A. González-Fernández, J. Juvert, M. Aceves-Mijares, A. Llobera, and C. Domínguez</i> | 1971 |
| Modeling and Simulation of Organic Photodetectors for Low Light Intensity Applications | <i>B. V. Popescu, D. H. Popescu, P. Lugli, S. Locci, F. Arca, S. F. Tedde, M. Sramek, and O. Hayden</i> | 1975 |
| Measurements and Simulations of Low Dark Count Rate Single Photon Avalanche Diode Device in a Low Voltage 180-nm CMOS Image Sensor Technology | <i>T. Leitner, A. Feininger, R. Turchetta, R. Coath, S. Chick, G. Visokolov, V. Savuskan, M. Javitt, L. Gal, I. Brouk, S. Bar-Lev, and Y. Nemirovsky</i> | 1982 |
| On-Chip FPN Calibration for a Linear-Logarithmic APS Using Two-Step Charge Transfer | <i>J. Lee, I. Baek, D. Yang, and K. Yang</i> | 1989 |
| Near-Infrared Photodetectors in Evaporated Ge: Characterization and TCAD Simulations | <i>V. Sorianello, A. De Iacovo, L. Colace, and G. Assanto</i> | 1995 |
| Solid-State Power and High Voltage Devices | | |
| Single-Event Burnout Hardening of Power UMOSFETs With Optimized Structure | <i>Y. Wang, Y. Zhang, L.-G. Wang, and C. Yu</i> | 2001 |
| Hot Carrier Injection Effects in the Ultrashallow Body SONOS Gate Power MOSFET | <i>X. Zhou, H. Feng, and J. K. O. Sin</i> | 2008 |
| Materials, Processing and Packaging | | |
| Accelerated Stress Test Assessment of Through-Silicon Via Using RF Signals | <i>C. Okoro, P. Kabos, J. Obrzut, K. Hummler, and Y. S. Obeng</i> | 2015 |
| Wafer-Level Integration of High-Quality Bulk Piezoelectric Ceramics on Silicon | <i>E. E. Aktakka, R. L. Peterson, and K. Najafi</i> | 2022 |

Solid State Device Phenomena

| | |
|--|------|
| Unified Endurance Degradation Model of Floating Gate NAND Flash Memory | 2031 |
| <i>A. Fayrushin, C.-H. Lee, Y. Park, J.-H. Choi, and C. Chung</i> | |
| Analysis of Single-Trap-Induced Random Telegraph Noise and Its Interaction With Work Function Variation for Tunnel FET | 2038 |
| <i>M.-L. Fan, V. P.-H. Hu, Y.-N. Chen, P. Su, and C.-T. Chuang</i> | |

Molecular and Organic Devices

| | |
|---|------|
| Organic Complementary Logic Circuits and Volatile Memories Integrated on Plastic Foils | 2045 |
| <i>M. Guerin, E. Bergeret, E. Bènevent, A. Daami, P. Pannier, and R. Coppard</i> | |
| Fast-Switching Printed Organic Electrochemical Transistors Including Electronic Vias Through Plastic and Paper Substrates | 2052 |
| <i>J. Kawahara, P. A. Ersman, K. Katoh, and M. Berggren</i> | |
| Frequency and Voltage Dependence of the Capacitance of MIS Structures Fabricated With Polymeric Materials | 2057 |
| <i>M. Estrada, F. Ulloa, M. Ávila, J. Sánchez, A. Cerdeira, A. Castro-Carranza, B. Iñiguez, L. F. Marsal, J. Pallarés</i> | |

Emerging Technologies and Devices

| | |
|--|------|
| Thermoelectric Performance of a Single-Layer Graphene Sheet for Energy Harvesting | 2064 |
| <i>R. Verma, S. Bhattacharya, and S. Mahapatra</i> | |
| Transconductance Linearity Analysis of 1-D, Nanowire FETs in the Quantum Capacitance Limit | 2071 |
| <i>A. Razavieh, D. B. Janes, and J. Appenzeller</i> | |

BRIEF PAPERS

| | |
|---|------|
| Dislocation Scattering in ZnMgO/ZnO Heterostructures | 2077 |
| <i>L. Sang, S. Y. Yang, G. P. Liu, G. J. Zhao, C. B. Liu, C. Y. Gu, H. Y. Wei, X. L. Liu, Q. S. Zhu, and Z. G. Wang</i> | |
| Transient Off-Current in Junctionless FETs | 2080 |
| <i>L. Barbut, F. Jazaeri, D. Bouvet, and J.-M. Sallese</i> | |
| Split-Gate-Enhanced Power UMOSFET With Soft Reverse Recovery | 2084 |
| <i>Y. Wang, W.-L. Jiao, H.-F. Hu, Y.-T. Liu, and J. Gao</i> | |
